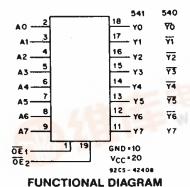
Technical Data

CD54/74AC540, CD54/74AC541 CD54/74ACT540, CD54/74ACT541



Data sheet acquired from Harris Semiconductor SCHS285A – Revised November 1999



Octal Buffer/Line Drivers, 3-State

CD74AC/ACT540 - Inverting CD74AC/ACT541 - Non-Inverting

Type Features:

- Buffered inputs
- Typical propagation delay: 4.5 ns @ V_{CC} = 5 V, T_A = 25° C, C_L = 50 pF

The CD54/74AC540, -541, and CD54/74ACT540, -541 octal buffer/line drivers use the RCA ADVANCED CMOS technology. The CD54/74AC/ACT540 are inverting 3-state buffers having two active-LOW output enables. The CD54/74AC/ACT541 are non-inverting 3-state buffers having two active-LOW output enables.

The CD74AC540, -541, and CD74ACT540, -541 are supplied in 20-lead dual-in-line plastic packages (E suffix) and in 20-lead dual-in-line small-outline plastic packages (M suffix). Both package types are operable over the following temperature ranges: Industrial (–40 to +85°C) and Extended Industrial/Military (–55 to +125°C).

The CD54AC540, -541, and CD54ACT540, -541, available in chip form (H suffix), are operable over the -55 to +125°C temperature range.

Family Features:

- Exceeds 2-kV ESD Protection MIL-STD-883, Method 3015
- SCR-Latchup-resistant CMOS process and circuit design
- Speed of bipolar FAST®/AS/S with significantly reduced power consumption
- Balanced propagation delays
- AC types feature 1.5-V to 5.5-V operation and balanced noise immunity at 30% of the supply.
- ± 24-mA output drive current
 - Fanout to 15 FAST® ICs
 - Drives 50-ohm transmission lines

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TRUTH TABLE

T WWY	CD54/74A	C/ACT540
INPUTS		OUTPUTS
OE1, OE2	Α	Υ
L	L	Н
Ļ	н	L
н	Х	. Z

H = High Voltage

L = Low Voltage

X = Immaterial

Z = High Impedance

TRUTH TABLE

	CD54/74AC/ACT541							
INPUTS		OUTPUTS						
OE1, OE2	A	Y COM						
L	L	W.075						
L	н	Н						
H	х	Z						



Technical Data

CD54/74AC540, CD54/74AC541 CD54/74ACT540, CD54/74ACT541

MAXIMUM RATINGS, Absolute-Maximum Values:
DC SUPPLY-VOLTAGE (V _{CC})
DC INPUT DIODE CURRENT, $I_{ K }$ (for $V_{ } < -0.5$ or $V_{ } > V_{CC} + 0.5$ V)
DC OUTPUT DIODE CURRENT, I_{OK} (for $V_O < -0.5$ or $V_O > V_{CC} + 0.5$ V)
DC OUTPUT SOURCE OR SINK CURRENT per Output Pin, IO (for $V_O > -0.5$ or $V_O < V_{CC} + 0.5$ V)
DC V _{CC} OR GROUND CURRENT (I _{CC} or I _{GND})
PACKAGE THERMAL IMPEDANCE, θ _{JA} (see Note 1): E package
M package
STORAGE TEMPERATURE (T _{Stq})65 to +150°C
LEAD TEMPERATURE (DURINĞ SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s maximum
Unit inserted into PC board min. thickness 1/16 in. (1.59 mm) with solder contacting lead tips only +300°C
* For up to 4 outputs per device: add ±25 mA for each additional output.

NOTE 1: The package thermal impedance is calculated in accordance with JESD 51.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, normal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIM	LIMITS		
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply-Voltage Range, V_{CC}^* : (For $T_A = Full Package-Temperature Range)$				
AC Types ACT Types	1.5 4.5	5.5 5.5	V	
DC Input or Output Voltage, V _I , V _O	0	Vcc	V	
Operating Temperature, T _A :	-55	+125	°C	
Input Rise and Fall Siew Rate, dt/dv at 1.5 V to 3 V (AC Types) at 3.6 V to 5.5 V (AC Types) at 4.5 V to 5.5 V (ACT Types)	0 0	50 20 10	ns/V ns/V	

^{*}Unless otherwise specified, all voltages are referenced to ground.

TERMINAL ASSIGNMENT DIAGRAMS



Technical Data	
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STATIC ELECTRICAL CHARACTERISTICS: AC Series

						AMBIENT TEMPERATURE (TA) - °C						
CHARACTERISTI	cs	TEST CONDITIONS		V _{cc}	+:	+25		o +85	-55 to +125		UNITS	
		V, (V)	l _o (mA)	(V)	MIN.	MAX.	MIN.	MAX.	MIN. MAX.			
High-Level Input				1.5	1.2	_	1.2		1.2			
Voltage	V _{iH}]	3	2.1	_	2.1		2.1		V	
				5.5	3.85	-	3.85	_	3.85		l	
Low-Level Input				1.5	_	0.3	_	0.3		0.3		
Voltage	VIL		ļ	3		0.9	_	0.9		0.9	V	
			1	5.5	-	1.65	_	1.65		1.65]	
High-Level Output			-0.05	1.5	1.4	l –	1.4	_	1.4	_		
Voltage	V_{OH}	ViH	-0.05	- 3	2.9		2.9		2.9	_]	
		or	-0.05	4.5	4.4	_	. 4.4	_	4.4	_]	
		VIL	-4	3	2.58	_	2.48		2.4	_] v	
			-24	4.5	3.94	_	3.8	_	3.7]	
		#, * {	-75	5.5			3.85	_	_			
		7, 1	-50	5.5	_	T			3.85	_	7	
Low-Level Output			0.05	1.5		0.1		0.1	_	0.1		
Voltage	Vol	VIH	0.05	3	_	0.1		0.1		0.1	1	
		or	0.05	4.5		0.1		0.1	_	0.1]	
		ViL	12	3		0.36	_	0.44	_	0.5	V	
			24	4.5	_	0.36	_	0.44	_	0.5	1	
		1	75	5.5	_		_	1.65		_	1	
		#. * }	50	5.5	-		_	_		1.65	1	
Input Leakage Current	l ₁	V _{cc} or GND		5.5	_	±0.1	_	±1	_	±1	μΑ	
3-State Leakage		ViH										
Current	loz	or					1					
		VıL		-			}		1			
		Vo =		5.5	_	±0.5	<u> </u>	±5		±10	μΑ	
		Vcc										
		or			ļ			ĺ		1		
		GND								l	1	
Quiescent Supply Current, MSI	lcc	V _{cc} or GND	0	5.5	_	8	_	80	_	160	μΑ	

[#]Test one output at a time for a 1-second maximum duration. Measurement is made by forcing current and measuring voltage to minimize nower dissination.

power dissipation.

* Test verifies a minimum 50-ohm transmission-line-drive capability at +85°C, 75 ohms at +125°C.

STATIC ELECTRICAL CHARACTERISTICS: ACT Series

				AMBIENT TEMPERATURE (TA) - °C]		
CHARACTERIST	ICS	TEST CONDITIONS		V _{cc}	+:	+25		o +85	-55 to +125		UNITS
		V, (V)	I _o (mA)	(V)	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.]
High-Level Input Voltage	V _{IH}			4.5 to 5.5	2	_	2	_	2	_	v
Low-Level Input Voltage	VIL			4.5 to 5.5		0.8	_	0.8	_	0.8	v
High-Level Output		ViH	-0.05	4.5	4.4	_	4.4		4.4		
Voltage	V _{OH}	or V _{IL}	-24	4.5	3.94		3.8		3.7		v
		#, ★ }	-75	5.5	_	_	3.85	_		_] '
		" }	-50	5.5	_	_			3.85	_]
Low-Level Output		V _{IH}	0.05	4.5	_	0.1	_	0.1	_	0:1	
Voltage	Vol	or V _{IL}	24	4.5	_	0.36	_	0.44	_	0.5	- v
		#, * {	75	5.5	_	_	_	1.65	_		
		\ "· `` }	50	5.5	_	_	_		_	1.65	1
Input Leakage Current	1,	V _{cc} or GND		5.5	_	±0.1	_	±1	_	±1	μА
3-State Leakage Current	loz	VIH or VIL Vo = Vcc or GND		5.5	_	±0.5		±5	_	±10	μΑ
Quiescent Supply Current, MSI	lcc	V _{cc} or GND	0	5.5	_	8	_	80		160	μΑ
Additional Quiescent Current per Input Pi TTL Inputs High 1 Unit Load	Supply in ΔI _{cc}	V _{cc} -2.1		4.5 to 5.5		2.4	_	2.8		3	mA

[#]Test one output at a time for a 1-second maximum duration. Measurement is made by forcing current and measuring voltage to minimize power dissipation.

ACT INPUT LOADING TABLE

INPUT	UNIT	LOAD*		
	540	541		
DATA	1.42	0.5		
OE1, OE2	1.3	1.3		

*Unit load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 2.4 mA max. @ 25° C.

^{*} Test verifies a minimum 50-ohm transmission-line-drive capability at +85°C, 75 ohms at +125°C.

SWITCHING CHARACTERISTICS: AC Series; t,, t, = 3 ns, C, = 50 pF

			AMBI	ENT TEMPE	RATURE (1	(A) - °C	T
CHARACTERISTICS	SYMBOL	v (v)	-40 t	-40 to +85		+125	UNITS
		(,	MIN.	MAX.	MIN.	MAX.	1
Propagation Delays: Data to Output AC540	tpLH tpHL	1.5 3.3* 5†	2.4 1.8	77 8.6 6.2	2.4 1.7	85 9.5 6.8	ns
AC541	t _{PLH} t _{PHL}	1.5 3.3 5	2.8 2.1	89 9.9 7.1	 2.7 2	98 10.9 7.8	ns
Enable, to Output to Output	t _{PZL} t _{PZH}	1.5 3.3 5	4.6 3.1	136 16.4 10.9	 4.5 3	150 18 12	ns
Disable to Output to Output	t _{PLZ} t _{PHZ}	1.5 3.3 5	3.9 3.1	136 13.6 10.9	— 3.8 3	150 15 12	ns
Power Dissipation Capacitance AC540 AC541	Сро‡			60 Typ. 60 Typ. 60 Typ. 60 Typ.			pF
Min. (Valley) V _{OH} During Switching of Other Outputs (Output Under Test Not Switching)	V _{онv} See Fig. 1	5	4 Typ. @ 25°C			V	
Max. (Peak) Vol. During Switching of Other Outputs (Output Under Test Not Switching)	V _{OLP} See Fig. 1	5	1 Typ. @ 25°C		٧		
Input Capacitance	Cı	_	_	10	_	10	pF
3-State Output Capacitance	Co	_	1 -	15	_	15	pF

SWITCHING CHARACTERISTICS: ACT Series; t,, t, = 3 ns, C, = 50 pF

	T		AMBI	ENT TEMPE	RATURE (T	ر (۲) - °C	
CHARACTERISTICS	SYMBOL	V _{cc} (V)	-40 1	o +85	-55 to	UNITS	
		(*)	MIN.	MAX.	MIN.	MAX.]
Propagation Delays: Data to Output ACT540	t _{PLH} t _{PHL}	5†	1.9	6.5	1.8	7.2	ns
ACT541	t _{PLH} t _{PHL}	5†	2.1	7.5	2.1	8.2	ns
Enable to Output	t _{PZL} t _{PZH}	5	3.5	12.2	3.4	13.4	ns
Disable to Output	t _{PLZ} t _{PHZ}	5	3.5	12.2	3.4	13.4	ns
Power Dissipation Capacitance ACT540 ACT541	C _{PO} §	_		Тур. Тур.	60 Typ. 60 Typ.		pF
Min. (Valley) V _{OH} During Switching of Other Outputs (Output Under Test Not Switching)	V _{онv} See Fig. 1	5	4 Typ. @ 25°C			. V	
Max. (Peak) Vol. During Switching of Other Outputs (Output Under Test Not Switching)	V _{OLP} See Fig. 1	5	1 Typ. @ 25°C		V		
Input Capacitance	Cı	_	_	10	_	10	ρF
3-State Output Capacitance	Co	. –		15	_	15	pF

*3.3 V: min. is @ 3.6 V max. is @ 3 V

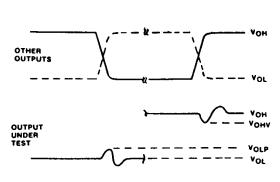
 C_{PD} is used to determine the dynamic power consumption, per channel. For AC series, $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ For ACT series, $P_D = V_{CC}^2 f_i (C_{PD} + C_L) + V_{CC} \Delta I_{CC}$ where $f_i = input free$

†5 V: min. is @ 5.5 V

 $\begin{aligned} & \textbf{f}_i = \text{input frequency} \\ & \textbf{C}_L = \text{output load capacitance} \end{aligned}$ V_{cc} = supply voltage.

max. is @ 4.5 V

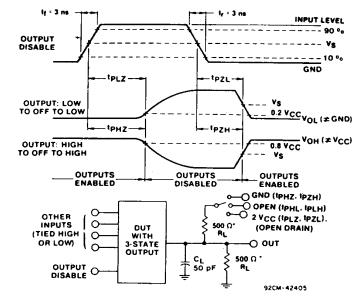
PARAMETER MEASUREMENT INFORMATION



NOTES:

- Vohy and volp are measured with respect to a ground reference near the output under test.
 Input pulses have the following characteristics:
- PRR \leq 1 MHz, t_f = 3 ne, t_f = 3 ne, SKEW 1 ne. 3. R.F. FIXTURE WITH 700-MHz DESIGN RULES REQUIRED. IC SHOULD BE SOLDERED INTO TEST BOARD AND BYPASSED WITH 0.1 JF CAPACITOR. SCOPE AND PROBES REQUIRE 700-MHz BANDWIDTH.

9205-42406



*FOR AC SERIES ONLY: WHEN VCC = 1.5 V, RL = 1 k Ω

Fig. 1 - Simultaneous switching transient waveforms.

Fig. 2 - Three-state propagation delay waveforms and test circuit.

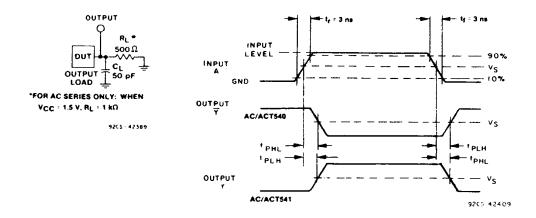


Fig. 3 - Propagation delay times and test circuit.

	CD54/74AC	CD54/74ACT
Input Level	V _{cc}	3 V
Input Switching Voltage, Vs	0.5 V _{cc}	1.5 V
Output Switching Voltage, Vs	0.5 V _{cc}	0.5 V _{cc}

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